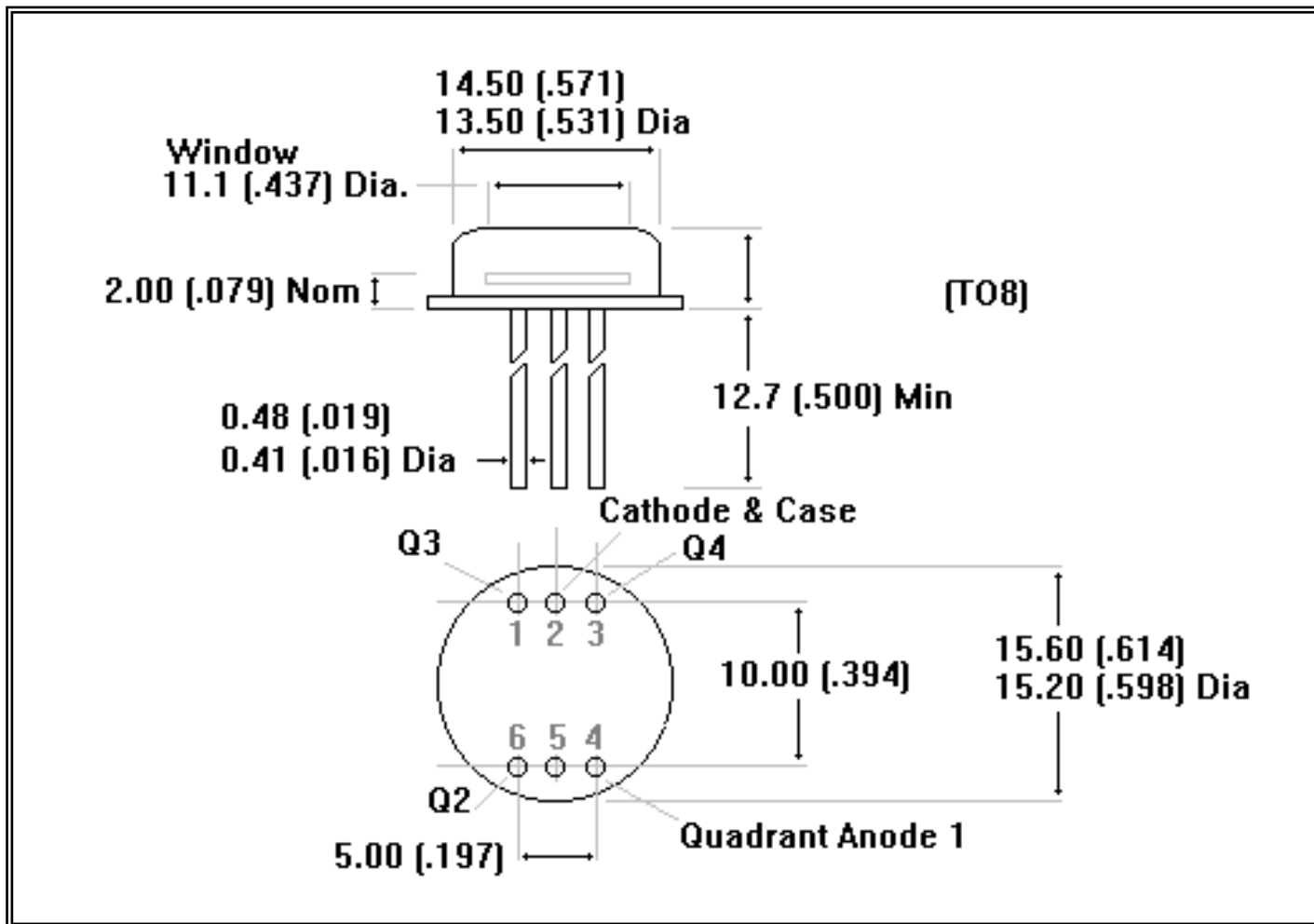


SILICON QUADRANT DETECTORS



SPECIFICATIONS

Part Numbers	S - 025 - QD
Active Area Overall	2.5 mm x 2.5 mm
Element Spacing	< 100 μ m
Dark Current ($V_R = 10V$)	5 nA
Shunt Capacitance (OV), per element	25 pf typ
NEP (950 nm, 1 kHz), $W/Hz^{1/2}$	< 10^{-14}
Rise Time	< 50 ns
Crosstalk	< 1%
Responsivity @ 950 nm, A/W	0.6